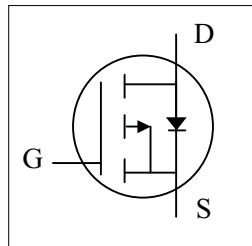


P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free

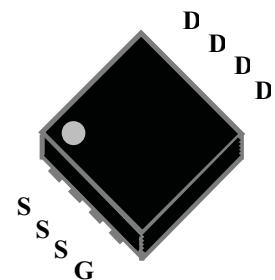


BV_{DSS}	-30V
$R_{DS(ON)}$	10m Ω
I_D	-14.6A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The PMPAK 3x3 package is special for DC-DC converters application and lower 1.0mm profile with backside heat sink.



PMPAK 3x3

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D@T_A=25^\circ C$	Drain Current ³ , V_{GS} @ 10V	-14.6	A
$I_D@T_A=70^\circ C$	Drain Current ³ , V_{GS} @ 10V	-11.7	A
I_{DM}	Pulsed Drain Current ¹	-50	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	3.12	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	5	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	40	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	-	-	10	mΩ
		V _{GS} =-4.5V, I _D =-6A	-	-	14.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	-	33	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-6A	-	34	54.4	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	9	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	12	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	11	-	ns
t _r	Rise Time	I _D =-1A	-	9	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	150	-	ns
t _f	Fall Time	V _{GS} =-10V	-	70	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	3800	6080	pF
C _{oss}	Output Capacitance	V _{DS} =-15V	-	500	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	345	-	pF
R _g	Gate Resistance	f=1.0MHz	-	9	18	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-2.6A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-10A, V _{GS} =0V,	-	27	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	16	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² 2oz copper pad of FR4 board, t ≤10sec ; 135°C/W when mounted on min. copper pad.

RATING AND CHARACTERISTICS CURVES (RMN3P10R0DN)

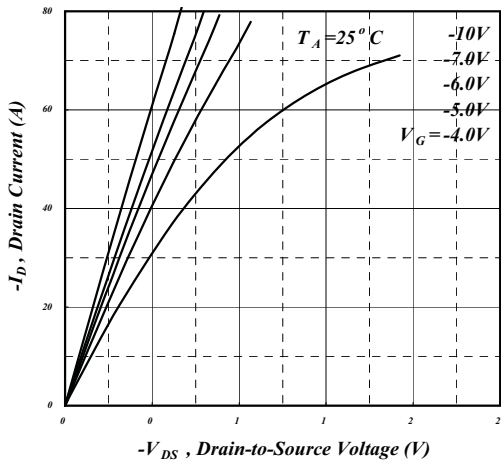


Fig 1. Typical Output Characteristics

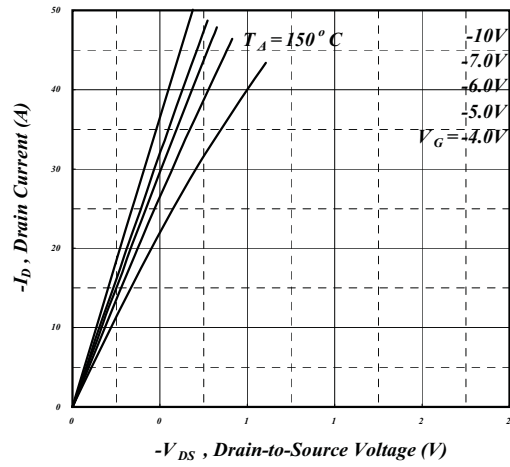


Fig 2. Typical Output Characteristics

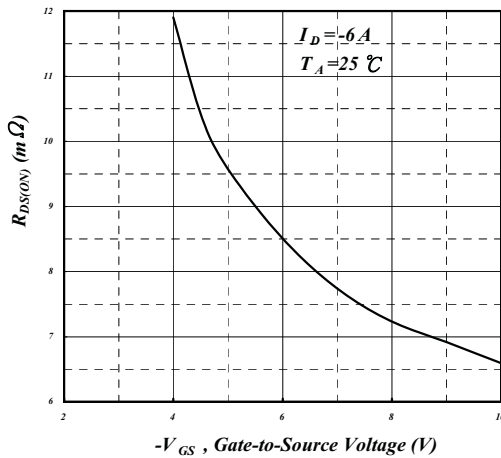


Fig 3. On-Resistance v.s. Gate Voltage

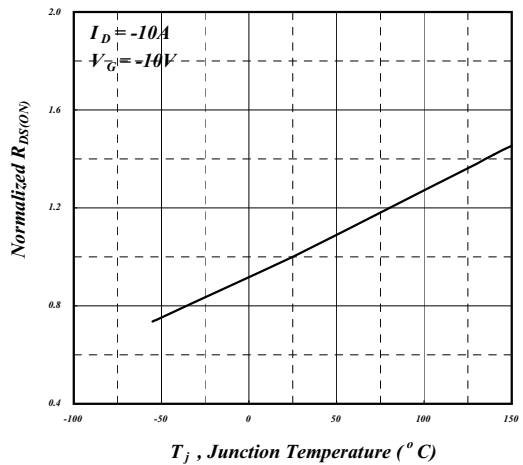


Fig 4. Normalized On-Resistance v.s. Junction Temperature

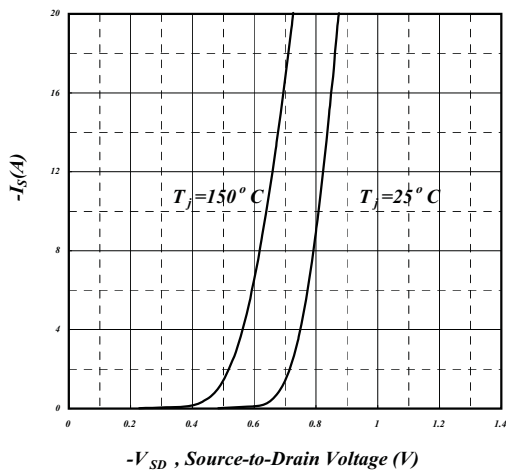


Fig 5. Forward Characteristic of Reverse Diode

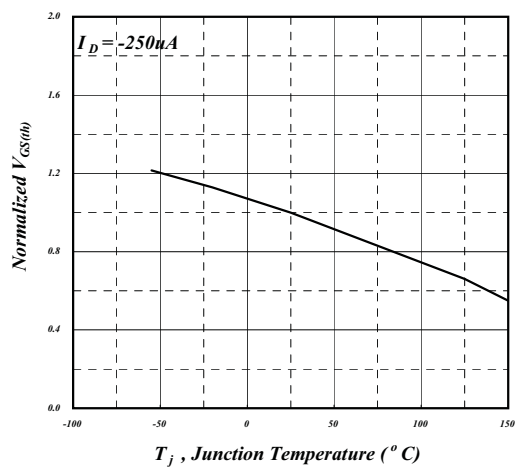


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

RATING AND CHARACTERISTICS CURVES (RMN3P10R0DN)

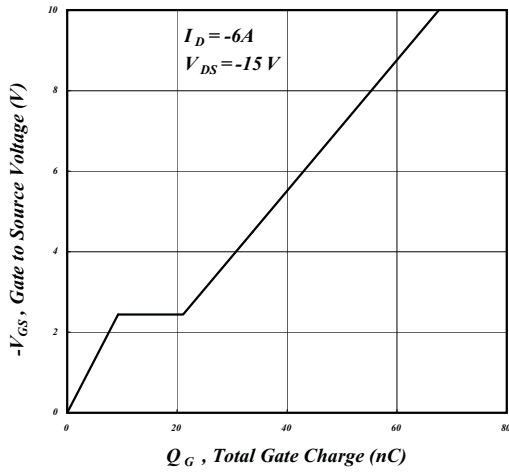


Fig 7. Gate Charge Characteristics

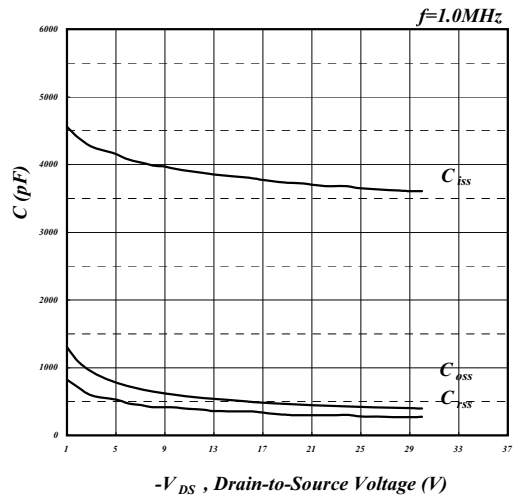


Fig 8. Typical Capacitance Characteristics

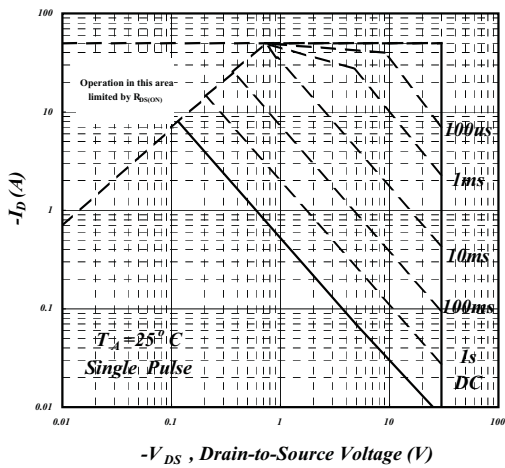


Fig 9. Maximum Safe Operating Area

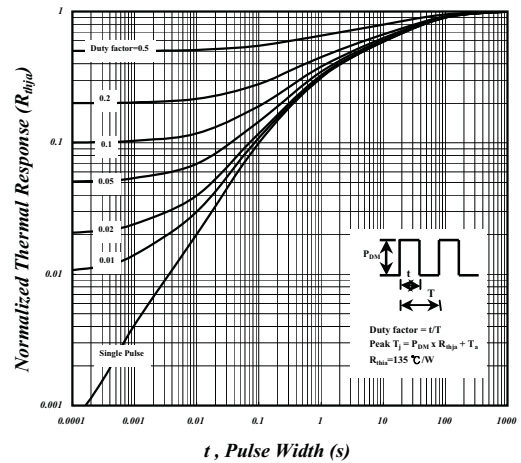


Fig 10. Effective Transient Thermal Impedance

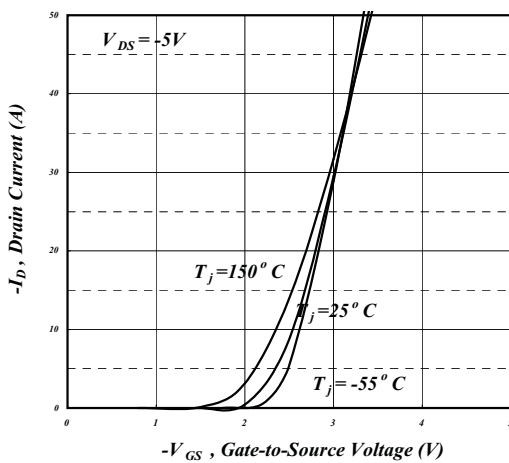


Fig 11. Transfer Characteristics

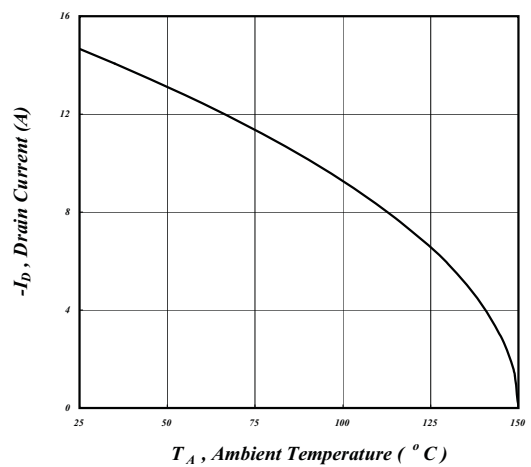
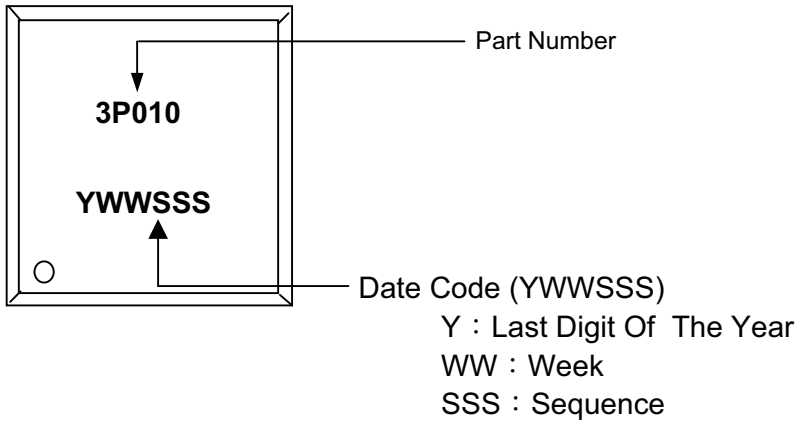
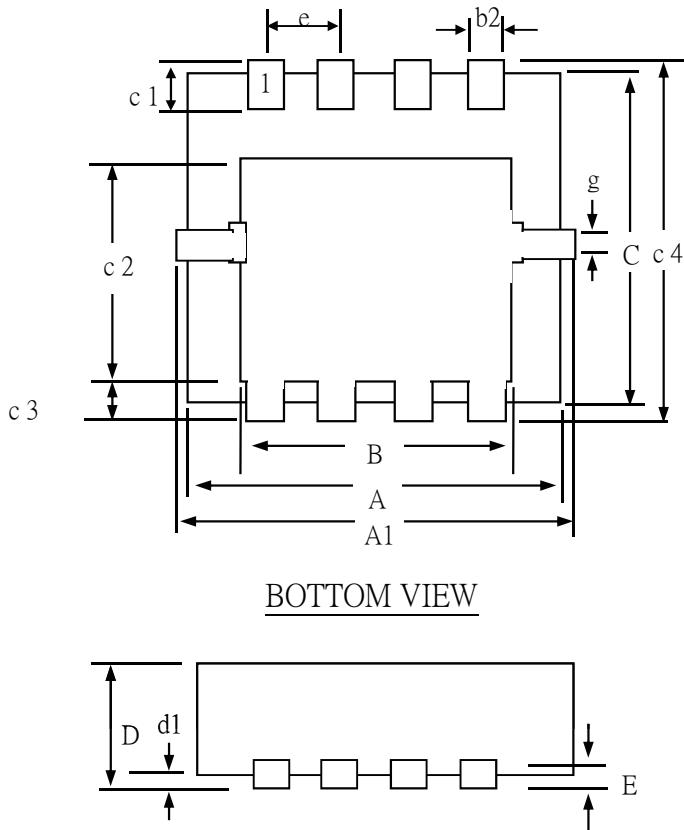


Fig 12. Drain Current v.s. Ambient Temperature

MARKING INFORMATION



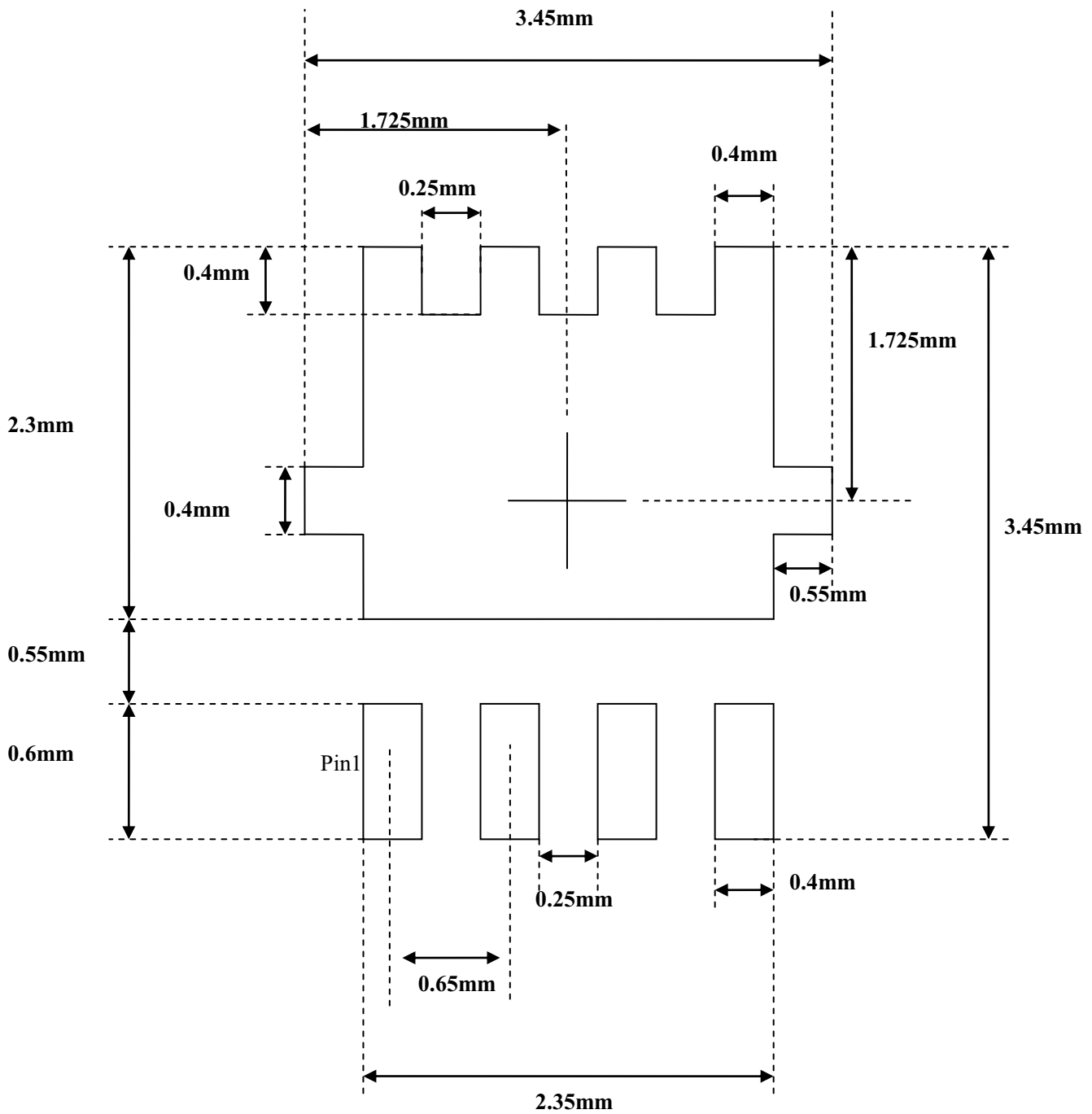
Package Outline : PMPAK 3x3



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.90	3.10	3.40
B	2.20	2.45	2.80
e	0.60	0.65	0.70
b2	0.20	0.30	0.40
C	2.90	3.10	3.40
c1	0.10	0.30	0.50
c2	1.20	1.70	2.20
c3	0.10	0.38	0.65
D	0.65	0.80	1.05
d1	0.00	0.10	0.20
E	0.10	0.18	0.25
A1	3.000	3.30	3.600
c4	3.000	3.30	3.600
g	0.20 (ref)		

- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

PMPAK3X3 FOOTPRINT :



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